

Fig. 1A

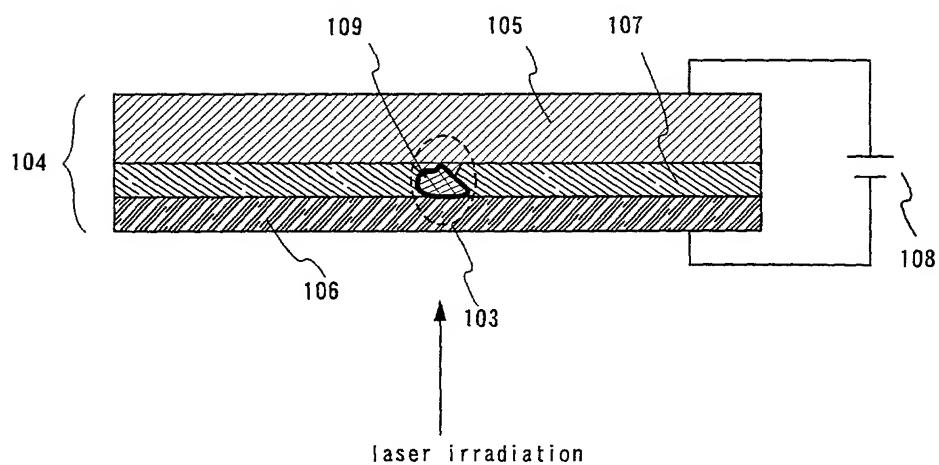


Fig. 1B

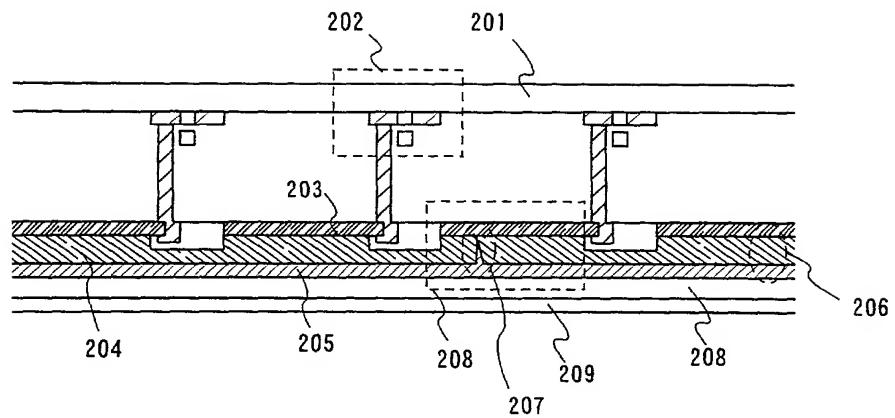


Fig. 2A

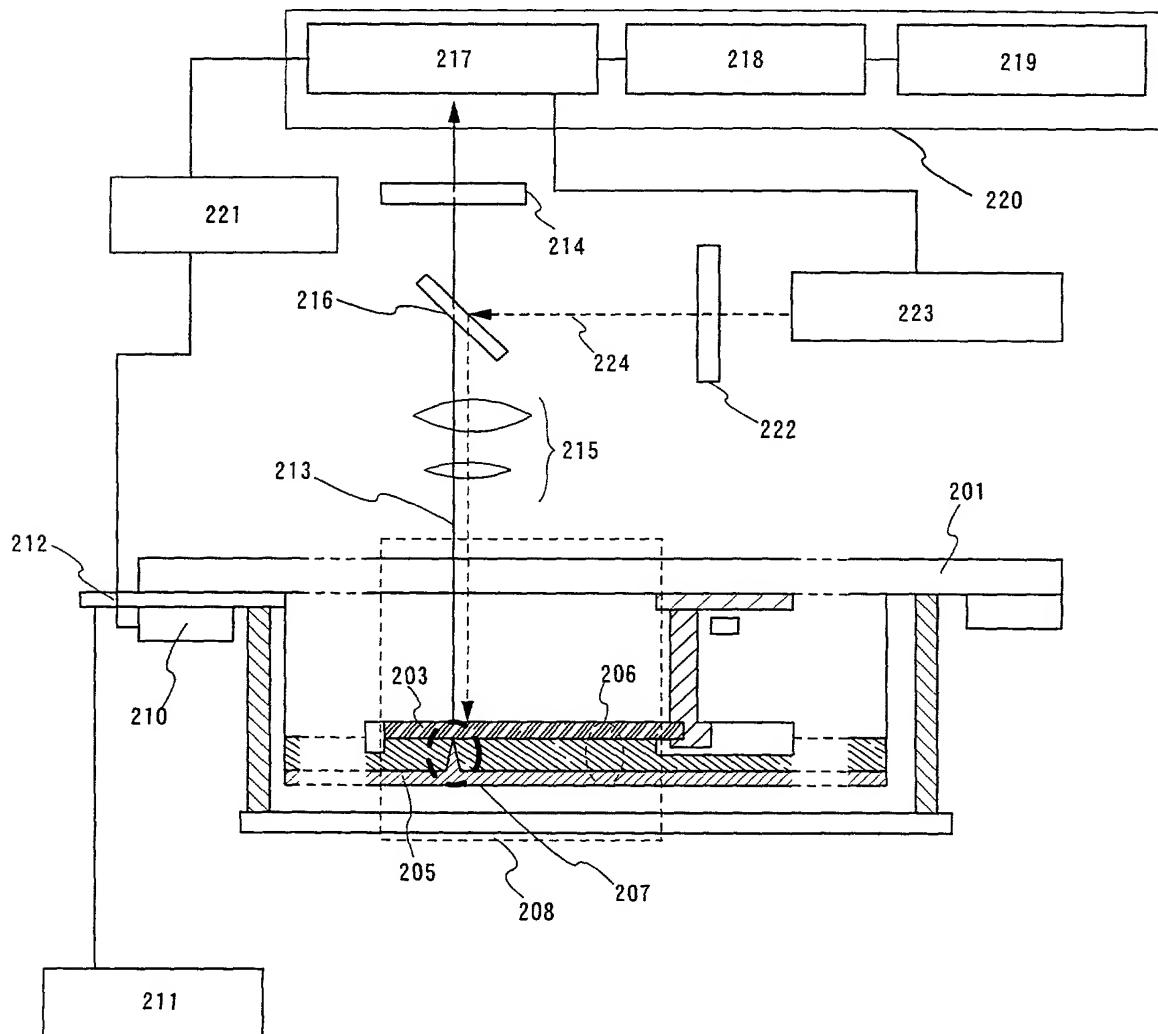


Fig. 2B

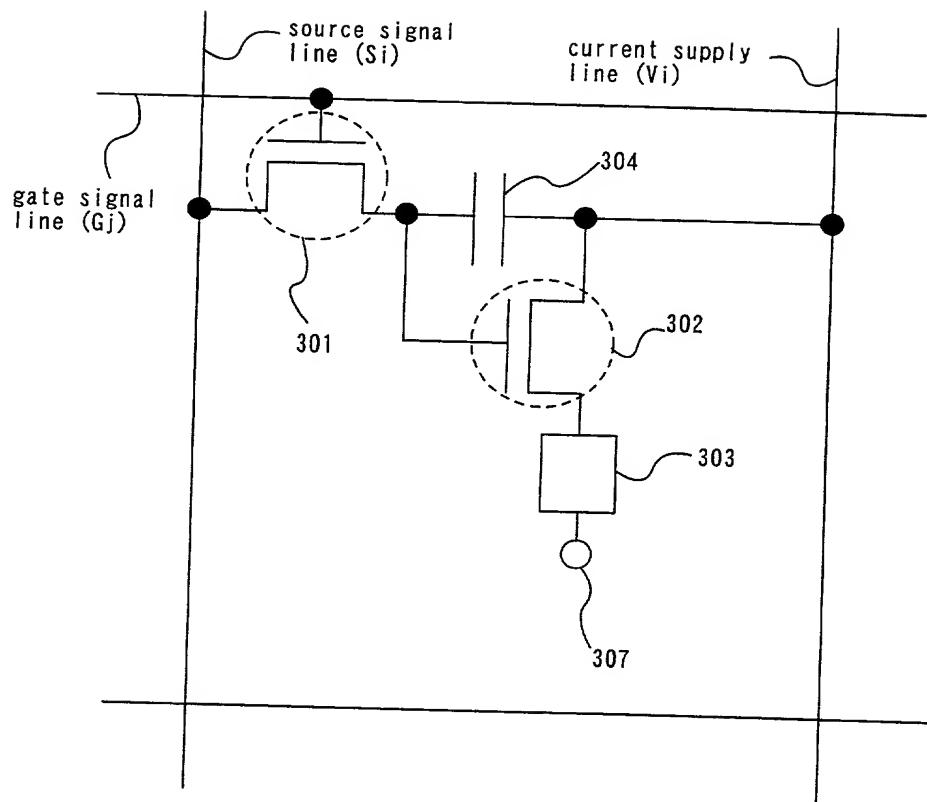


Fig. 3

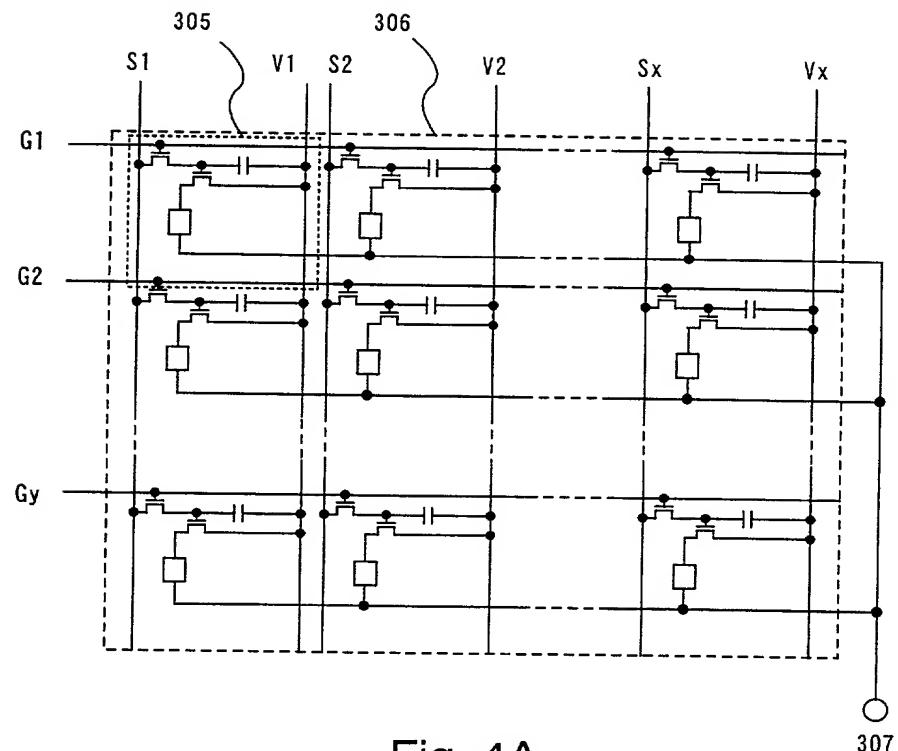


Fig. 4A

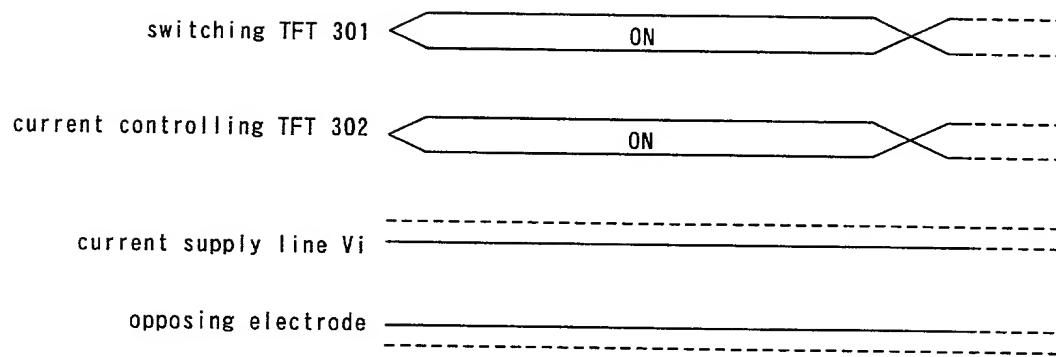
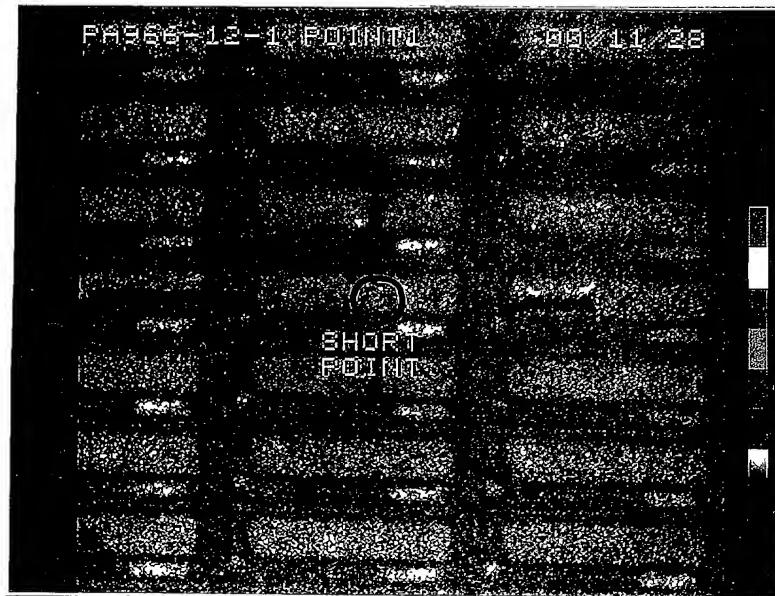
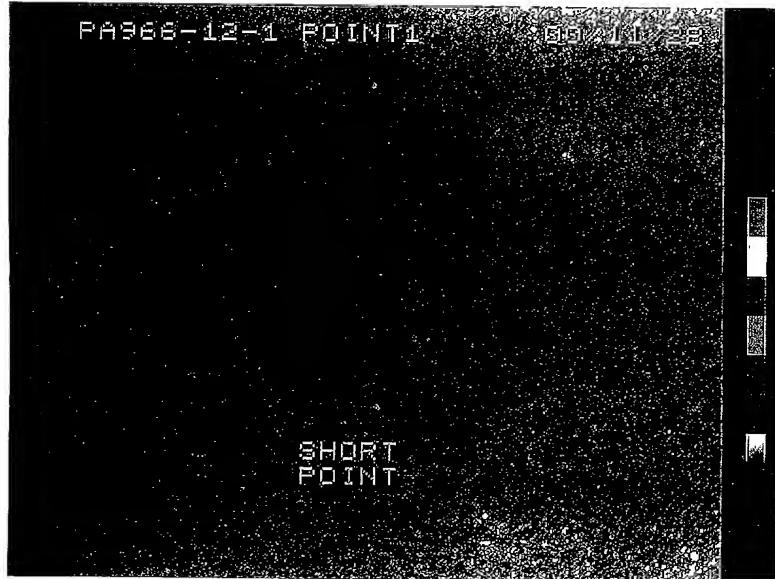


Fig. 4B



×200

Fig. 5A



×500

Fig. 5B

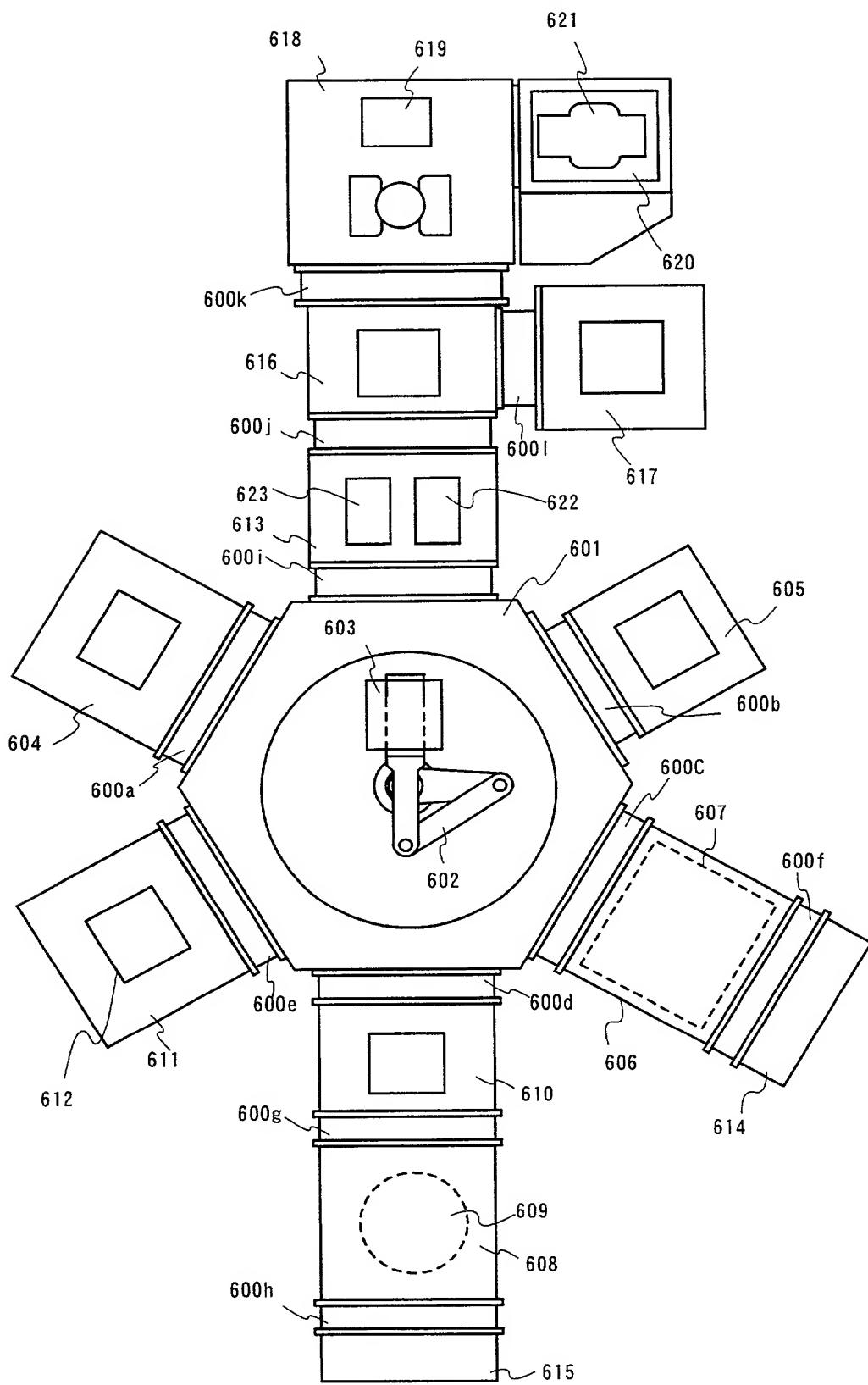


Fig. 6

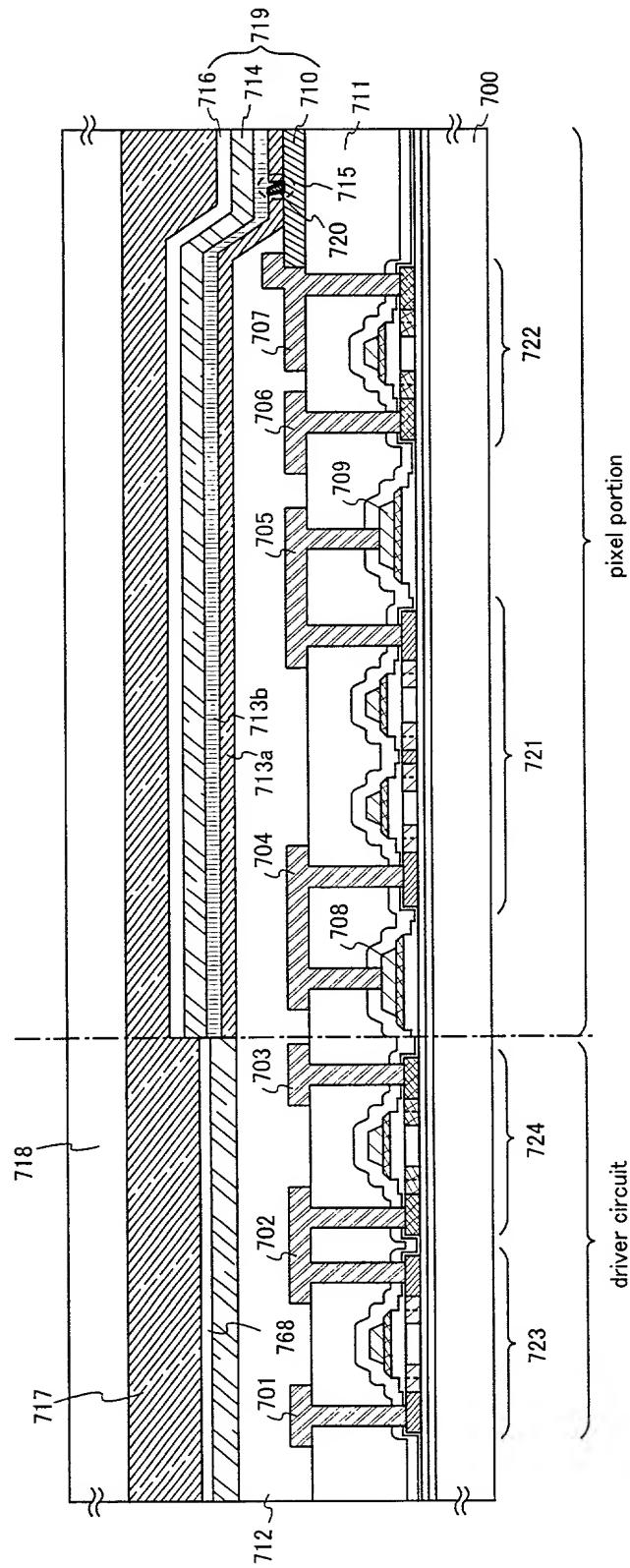
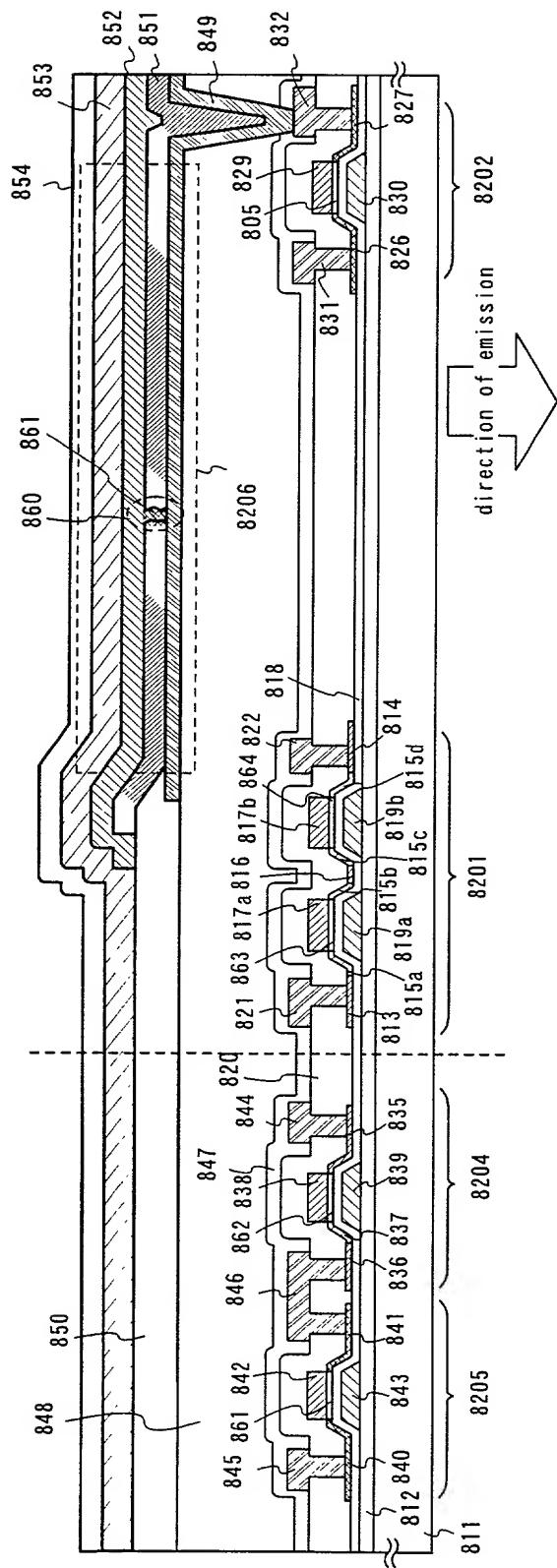


Fig. 7



8
Fig.

811:substrate 812:base film 813:source region 814:drain region 815a~815d:LDU region 816:separation region 817a, 17b:channel formation region 818:gate insulating film 819a, 819b:gate electrodes 820:first interlayer insulating film 821:source signal line 822:drain wiring 826:source region 827:drain region 828:LDU region 829:channel formation region 830:gate electrode 831:source wiring 832:drain wiring 835:source region 836:drain region 837:LDU region 838:channel formation region 839:gate electrode 840:source region 841:drain region 842:channel formation region 843:gate electrode 844, 845:source wirings 846:drain wiring 847:first passivation film 848:second interlayer insulating film 849:pixel electrode (anode) 850:third interlayer insulating film 851:organic compound layer 852:cathode 853:protecting electrode 854:second passivation film

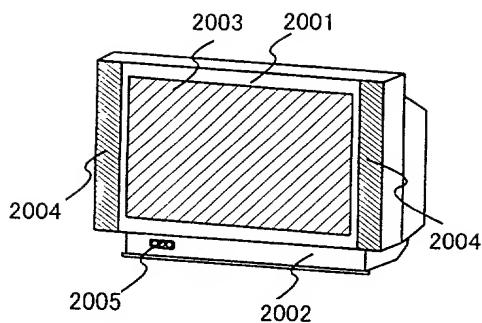


Fig. 9A

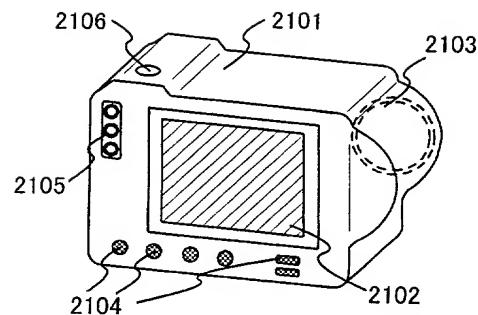


Fig. 9B

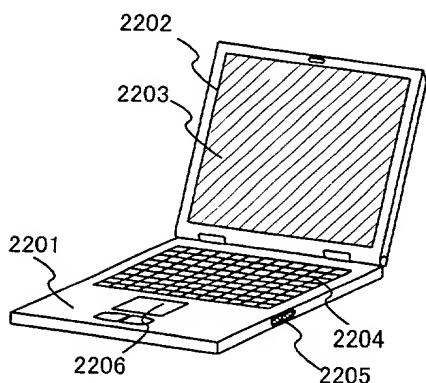


Fig. 9C

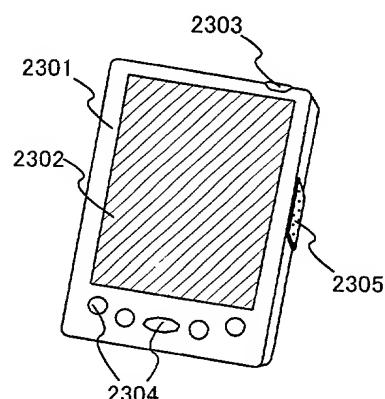


Fig. 9D

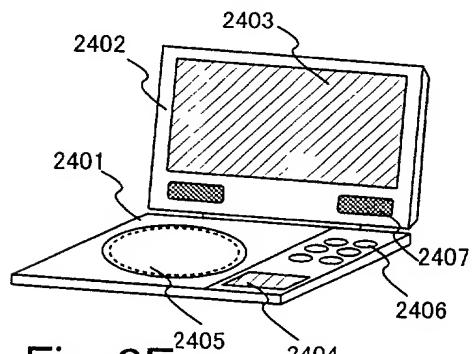


Fig. 9E

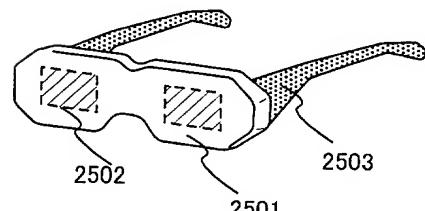


Fig. 9F

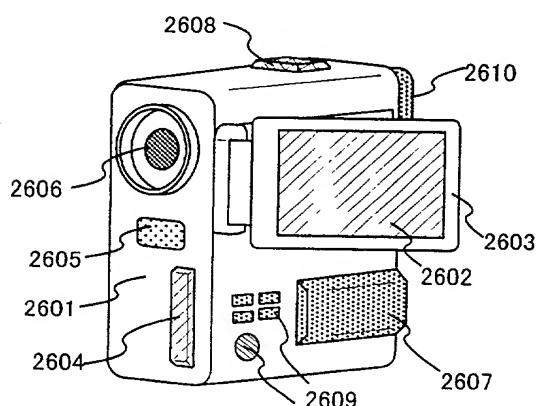


Fig. 9G

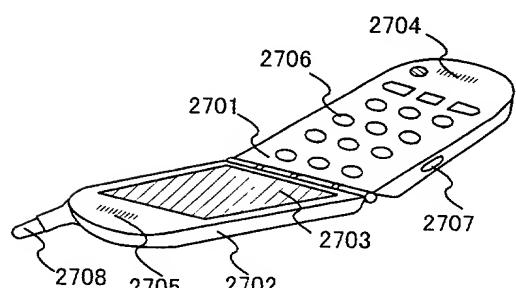


Fig. 9H

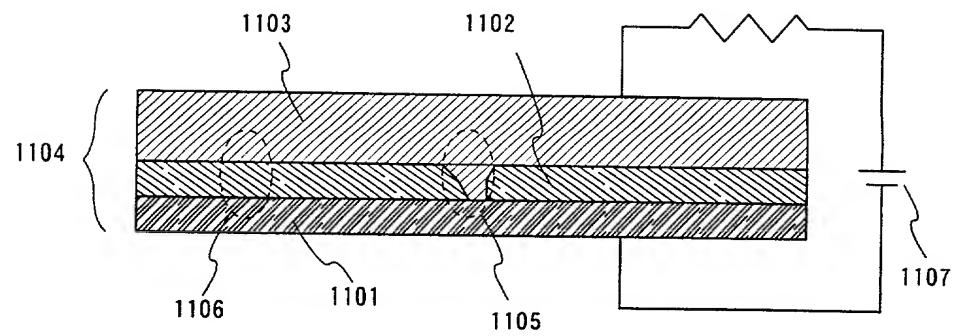


Fig. 10A

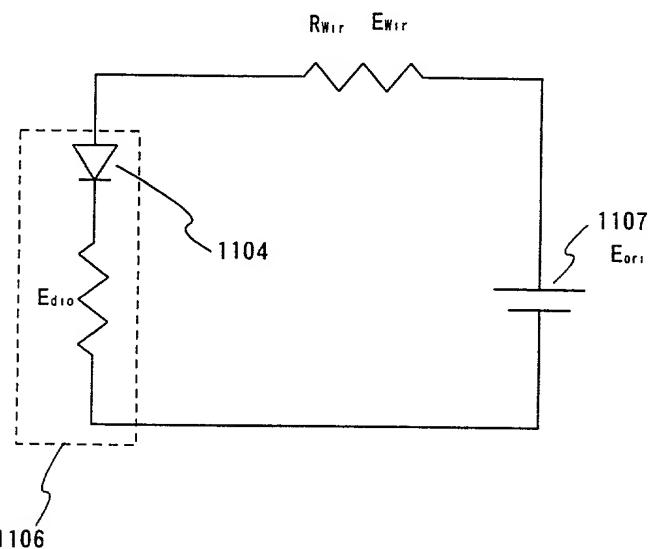


Fig. 10B

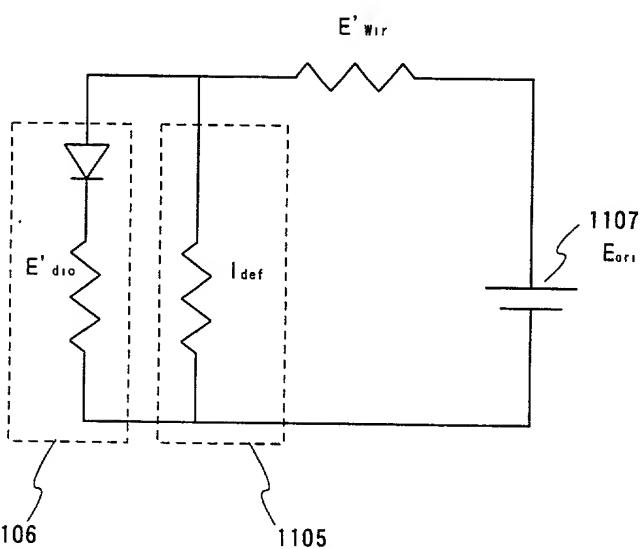


Fig. 10C

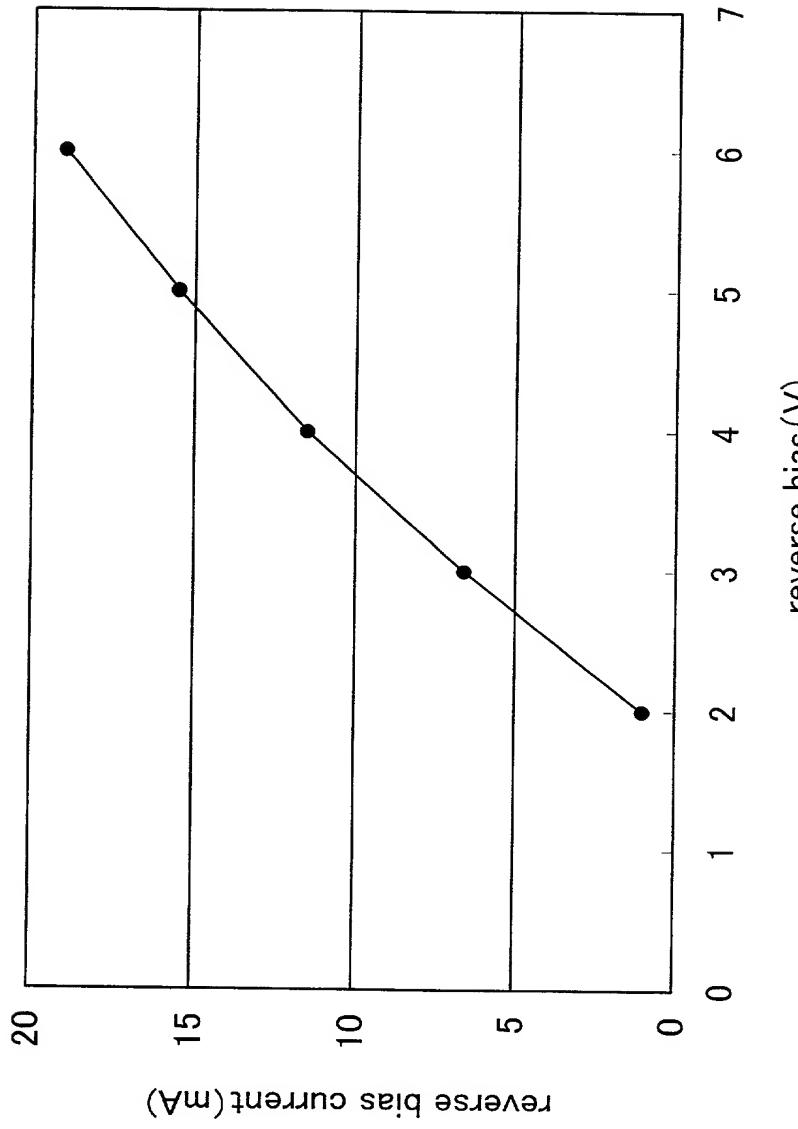


Fig. 11 Current property when a backward bias voltage is applied to a light emitting element